

INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

(PTO-1449)

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57810-084SERIAL NO.
Divisional of Appl No.
10/084,050APPLICANT
Nobuhiko HAYASHI, et al.FILING DATE
March 10, 2004

GROUP

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
<i>Dh</i>		US 6,015,979	1/18/2000	Sugiura et al.	—
		US 6,051,849	4/18/2000	Davis et al.	—
		US 6,503,769	01/07/2003	Nakamura et al.	—
		US			
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EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number + Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
<i>Dh</i>		2000-184959	6/16/2000	—	—	Japan (w/ English Abstract)	
		2000-269144	9/29/2000	—	—	Japan (w/ English Abstract)	
		2000-21789	1/21/2000	—	—	Japan (w/ English Abstract)	
<i>Dh</i>		10-312871	11/24/1998	—	—	Japan (w/ English Abstract)	

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<i>Dh</i>		S. Nakamura et al., "Long lifetime violet InGaN/GaN/A1GaN-based semiconductor lasers", Journal of Oyo Denshi Bussel Bunkakai, Vol. 4, (1988), pp. 53-58 and 210-215.
		Akira Usui et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy", Jpn. J. Appl. Phys. Vol. 36 (1997), pp. L899-L902.
		Kevin Linthicum et al., "Pseudoepitaxy of gallium nitride thin films", Applied Physics Letter, Vol. 75, No. 2, July 12, 1999, pp. 198-199.
<i>Dh</i>		Isao Kidoguchi et al., "Air-bridged lateral epitaxial overgrowth of GaN thin films", Applied Physics Letter, Vol. 76, No. 25, June 19, 2000, pp. 3788-3790.

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 57810-084	SERIAL NO. Divisional of Appl No. 10/084,050 <i>10/796154</i>	
				APPLICANT Nobuhiko HAYASHI, et al.		
FILING DATE March 10, 2004				GROUP 2818		
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	
<i>Dle</i>		US 6,015,979	1/18/2000	Sugiura et al.	—	
<i>Dle</i>		US 6,051,849	4/18/2000	Davis et al.	—	
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<i>Dle</i>		US			—	
<i>Dle</i>		US			—	
FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code-Number -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation
					Yes	No
<i>Dle</i>		2000-164989	6/16/2000	—	—	Japan (w/ English Abstract)
<i>Dle</i>		2000-269144	9/29/2000	—	—	Japan (w/ English Abstract)
<i>Dle</i>		2000-21789	1/21/2000	—	—	Japan (w/ English Abstract)
<i>Dle</i>		10-312971	11/24/1998	—	—	Japan (w/ English Abstract)
ARTICLES OF OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)						
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
<i>Dle</i>		S. Nakamura et al., "Long lifetime violet InGaN/GaN/AlGaN-based semiconductor lasers", Journal of Oyo Denshi Bussel Bunkakai, Vol. 4, (1998), pp. 53-58 and 210-215.				
<i>Dle</i>		Akira Usui et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy", Jpn. J. Appl. Phys. Vol. 36 (1997), pp. L889-L892.				
<i>Dle</i>		Kevin Linthicum et al., "Pseudoepitaxy of gallium nitride thin films", Applied Physics Letter, Vol. 75, No. 2, July 12, 1999, pp. 196-198.				
<i>Dle</i>		Isao Kidoguchi et al., "Air-bridged lateral epitaxial overgrowth of GaN thin films", Applied Physics Letter, Vol. 76, No. 25, June 19, 2000, pp. 3768-3770.				
EXAMINER <i>Dle</i>			DATE CONSIDERED <i>OCT - 2005</i>			

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